## Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

## Listing of Claims:

Claim 1 (previously presented): Ultrahigh purity copper having a residual resistance ratio of 38,000 or greater and a purity of 8N or higher, gas components of O, C, N, H, S and P being excluded from a determination of said purity, and a content of impurities in said ultrahigh purity copper excluding said gas components totaling no more than 0.01ppm.

Claim 2 (original): The ultrahigh purity copper according to claim 1, wherein the respective elements of O, C, N, H, S and P as gas components are 1ppm or less.

## Claims 3-6 (canceled).

Claim 7 (currently amended): An ultrahigh purity copper according to claim 1, prepared by a process comprising the steps of, upon subjecting copper to high purification with an electrolytic method, partitioning an anode and a cathode an electrolytic bath with an anion exchange membrane into an anode side and a cathode side of the electrolytic bath, intermittently or continuously extracting an anolyte from the anode side of said electrolytic bath, pouring in and agitating adding active carbon into the extracted anolyte and agitating the extracted anolyte to absorb impurities to the active carbon, removing the absorbed impurities together with the active carbon from the extracted anolyte by filtration[,] obtaining to obtain a high purity copper electrolytic solution, and intermittently or continuously introducing pouring the high purity

copper electrolytic solution into the cathode side of the electrolytic bath, and electrolyzing the high purity copper electrolytic solution.

Claim 8 (previously presented): An ultrahigh purity copper according to claim 7, wherein the respective elements of O, C, N, H, S and P as gas components are 1ppm or less.

Claim 9 (previously presented): An ultrahigh purity copper according to claim 2, wherein the content of silver (Ag) in said ultrahigh purity copper is less than 0.005ppm, wherein the content of aluminum (Al) in said ultrahigh purity copper is less than 0.001ppm, and said content of iron (Fe) in said ultrahigh purity copper is less than 0.001ppm.

Claim 10 (previously presented): An ultrahigh purity copper according to claim 1, wherein the content of silver (Ag) in said ultrahigh purity copper is less than 0.005ppm, wherein the content of aluminum (Al) in said ultrahigh purity copper is less than 0.001ppm, and said content of iron (Fe) in said ultrahigh purity copper is less than 0.001ppm.

Claim 11 (new): An ultrahigh purity copper according to claim 9, wherein the residual resistance ratio of the ultrahigh purity copper is 40,000 to 100,000.

Claim 12 (new): An ultrahigh purity copper according to claim 11, wherein the purity of the ultrahigh purity copper is higher than 8N.

Claim 13 (new): An ultrahigh purity copper according to claim 11, wherein the purity of the ultrahigh purity copper is 9N.

Claim 14 (new): An ultrahigh purity copper according to claim 11, wherein a content of sulfur (S) in the ultrahigh purity copper is less than 0.005ppm.

Claim 15 (new): A copper sputtering target having superior deposition characteristics made from the ultrahigh purity copper according to claim 14.